

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	23607	SOI (silicon near on near insulator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/02 15:27
L3	78866	(MOSFET (Metal near oxide near semiconductor near field near effect near transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 15:33
L4	541	channel with (fully near deplet\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 15:34
L5	259	2 and 3 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 15:34